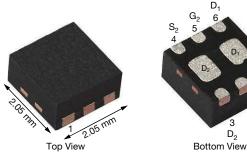


www.vishay.com

Dual N-Channel 20 V (D-S) MOSFET

PowerPAK® SC-70-6L Dual

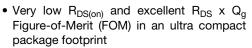


Marking code: A7

PRODUCT SUMMARY	
V _{DS} (V)	20
$R_{DS(on)}$ max. (Ω) at $V_{GS} = 10 \text{ V}$	0.0215
$R_{DS(on)}$ max. (Ω) at $V_{GS} = 4.5 \text{ V}$	0.0245
$R_{DS(on)}$ max. (Ω) at $V_{GS} = 2.5 \text{ V}$	0.048
Q _g typ. (nC)	3.5
I _D (A) ^a	4.5
Configuration	Dual

FEATURES

• TrenchFET® Gen IV power MOSFET

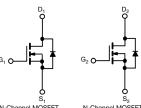




- · Compact and thermally enhanced package
- · Provides exceptional versatility for power management
- · Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

APPLICATIONS

- Synchronous rectification
- Half-bridge power stage
- DC/DC converters
- · Battery management
- Load switch



ORDERING INFORMATION						
Package	PowerPAK SC-70					
Lead (Pb)-free and halogen-free	SiA938DJT-T1-GE3					

ABSOLUTE MAXIMUM RATING	S (T _A = 25 °C, u	nless other	wise noted)		
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-source voltage		V_{DS}	20	V	
Gate-source voltage		V_{GS}	+12 / -8	7 v	
	T _C = 25 °C		4.5 ^a		
Continuous dusin automat (T. 150 °C)	T _C = 70 °C	I _D	4.5 ^a	1	
Continuous drain current (T _J = 150 °C)	T _A = 25 °C		4.5 ^{a, b, c}	1	
	T _A = 70 °C		4.5 ^{a, b, c}	A	
Pulsed drain current		I _{DM}	30		
Continuous source dusin diada surrent	T _C = 25 °C		4.5 ^a		
Continuous source-drain diode current	T _A = 25 °C	l _S	1.6 ^{b, c}	1	
	T _C = 25 °C		7.8		
Maximum power dissipation	T _C = 70 °C	P _D	5	\Box w	
Maximum power dissipation	T _A = 25 °C		1.9 b, c		
	T _A = 70 °C		1.2 ^{b, c}	<u> </u>	
Operating junction and storage temperature	e range	T _J , T _{stg}	-55 to +150	-°C	
Soldering recommendations (peak tempera	ture) ^{d, e}		260		

THERMAL RESISTANCE RATINGS									
PARAMETER		SYMBOL	TYPICAL	MAXIMUM	UNIT				
Maximum junction-to-ambient b, f	t ≤ 5 s	R_{thJA}	52	65	°C/W				
Maximum junction-to-case (drain)	Steady state	R_{thJC}	12.5	16	C/VV				

Notes

- a. Package limited
- b. Surface mounted on 1" x 1" FR4 board
- See solder profile (www.vishay.com/doc?73257). The PowerPAK SC-70 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- Rework conditions: manual soldering with a soldering iron is not recommended for leadless components
- Maximum under steady state conditions is 110 °C/W

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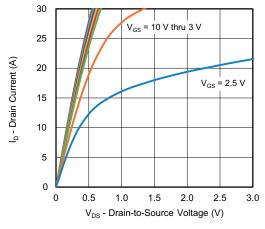
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static	'				L	
Drain-source breakdown voltage	V_{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	20	-	-	V
V _{DS} temperature coefficient	$\Delta V_{DS}/T_{J}$	J 050 A	-	13	-	mV/°C
V _{GS(th)} temperature coefficient	$\Delta V_{GS(th)}/T_J$	I _D = 250 μA	-	-3.3	-	
Gate-source threshold voltage	V _{GS(th)}	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$	0.6	-	1.5	V
Gate-source leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = +12 V / -8 V	-	-	± 100	nA
		V _{DS} = 20 V, V _{GS} = 0 V	-	-	1	
Zero gate voltage drain current	I _{DSS}	V _{DS} = 20 V, V _{GS} = 0 V, T _J = 55 °C	-	-	10	μA
On-state drain current a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	5	-	-	Α
	2(0.1)	$V_{GS} = 10 \text{ V}, I_D = 5 \text{ A}$	-	0.0170	0.0215	
Drain-source on-state resistance a	R _{DS(on)}	V _{GS} = 4.5 V, I _D = 5 A	-	0.0190	0.0245	Ω
	23(6.1)	V _{GS} = 2.5 V, I _D = 3 A	_	0.0300	0.0480	
Forward transconductance a	9 _{fs}	V _{DS} = 10 V, I _D = 10 A	-	28	-	S
Dynamic ^b	<u> </u>	50 . 5				
Input capacitance	C _{iss}		_	425	_	
Output capacitance	C _{oss}	$V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	-	150	-	pF
Reverse transfer capacitance	C _{rss}	, de ,	-	30	-	
·		$V_{DS} = 10 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 5 \text{ A}$	-	7.6	11.5	nC
Total gate charge	Qg	<u> </u>	-	3.5	5.3	
Gate-source charge	Q _{gs}	$V_{DS} = 10 \text{ V}, V_{GS} = 4.5 \text{ V}, I_{D} = 5 \text{ A}$	-	1.2	-	
Gate-drain charge	Q _{ad}	20 1 , de 1 , b	-	0.63	-	
Gate resistance R _q		f = 1 MHz	0.6	2.8	5.6	Ω
Turn-on delay time	t _{d(on)}		-	11	22	
Rise time	t _r	$V_{DD} = 10 \text{ V}, R_L = 1 \Omega$	-	25	50	ns
Turn-off delay time	t _{d(off)}	$I_D \cong 5 \text{ A}, V_{GEN} = 4.5 \text{ V}, R_g = 1 \Omega$	-	16	35	
Fall time	t _f		-	7	15	
Turn-on delay time	t _{d(on)}		-	6	15	
Rise time	t _r	$V_{DD} = 10 \text{ V}, R_{I} = 1 \Omega$	-	5	10	
Turn-off delay time	t _{d(off)}	$I_D \cong 5 \text{ A}, V_{GEN} = 10 \text{ V}, R_q = 1 \Omega$	-	15	30	
Fall time	t _f	u(on)			10	1
Drain-Source Body Diode Characteristic	· · ·					
Continuous source-drain diode current	Is	T _C = 25 °C	l -	_	4.5	
Pulse diode forward current	I _{SM}	.0 20 0	-	_	30	Α
Body diode voltage V _{SD}		I _S = 5 A, V _{GS} = 0 V	-	0.82	1.2	V
Body diode reverse recovery time t _{rr}		.0 0.4, .00 0.	-	9	20	ns
Body diode reverse recovery three	Q _{rr}	$I_F = 5 \text{ A, di/dt} = 100 \text{ A/µs,}$	_	2	5	nC
Reverse recovery fall time	t _a	$T_{F} = 5 \text{ A}, \text{ d}/\text{d}t = 100 \text{ A}/\mu\text{s},$ $T_{A} = 25 \text{ °C}$	_	4.8	-	 ,
Tieverse receivery fail tillie	ча	.0 _0 0	<u> </u>	7.0	<u> </u>	ns

Notes

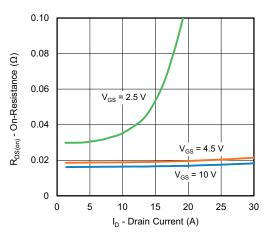
- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %
- b. Guaranteed by design, not subject to production testing

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

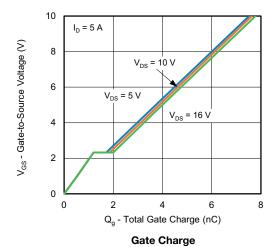


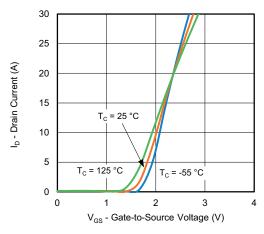


Output Characteristics

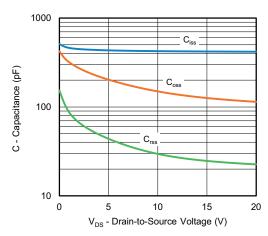


On-Resistance vs. Drain Current and Gate Voltage

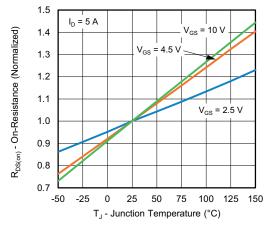




Transfer Characteristics

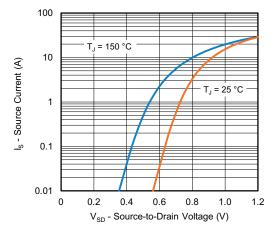


Capacitance

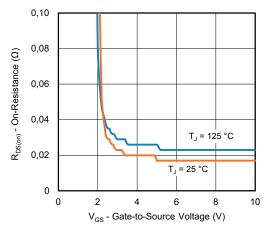


On-Resistance vs. Junction Temperature

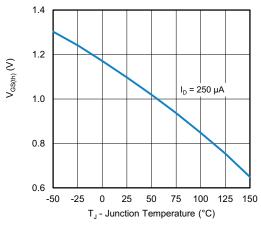




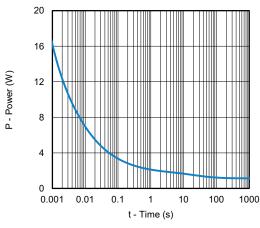
Source-Drain Diode Forward Voltage



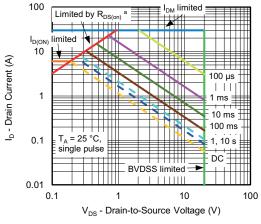
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



Single Pulse Power (Junction-to-Ambient)

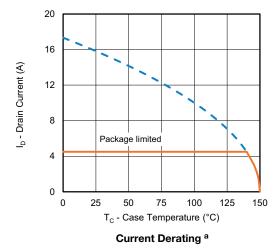


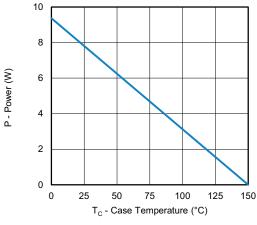
Safe Operating Area, Junction-to-Ambient

Note

a. V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified





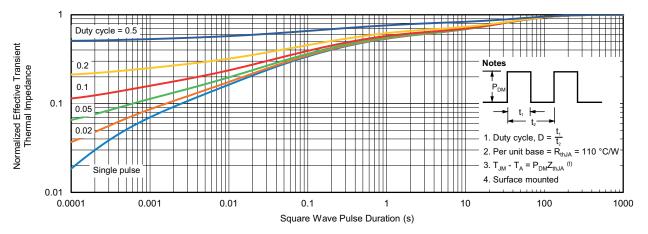


Power Derating

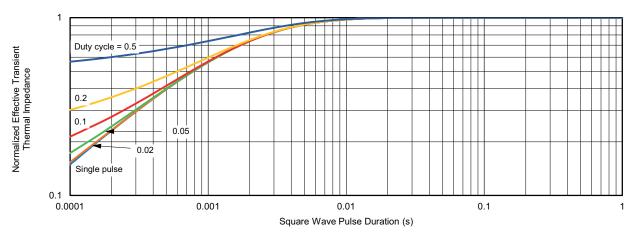
Note

a. The power dissipation P_D is based on T_J max. = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.





Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

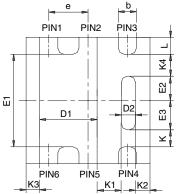
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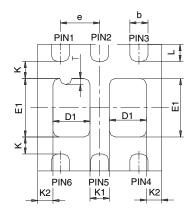




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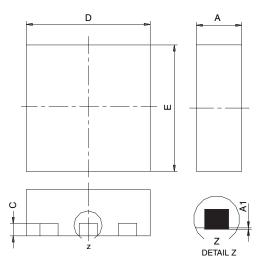
PowerPAK® SC70-6L





BACKSIDE VIEW OF SINGLE

BACKSIDE VIEW OF DUAL



- All dimensions are in millimeters
 Package outline exclusive of mold flash and metal burr
 Package outline inclusive of plating

	SINGLE PAD							DUAL PAD					
DIM	M	ILLIMETER	RS	INCHES		М	ILLIMETER	RS	INCHES				
	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max	
Α	0.675	0.75	0.80	0.027	0.030	0.032	0.675	0.75	0.80	0.027	0.030	0.032	
A 1	0	-	0.05	0	-	0.002	0	-	0.05	0	-	0.002	
b	0.23	0.30	0.38	0.009	0.012	0.015	0.23	0.30	0.38	0.009	0.012	0.015	
С	0.15	0.20	0.25	0.006	0.008	0.010	0.15	0.20	0.25	0.006	0.008	0.010	
D	1.98	2.05	2.15	0.078	0.081	0.085	1.98	2.05	2.15	0.078	0.081	0.085	
D1	0.85	0.95	1.05	0.033	0.037	0.041	0.513	0.613	0.713	0.020	0.024	0.028	
D2	0.135	0.235	0.335	0.005	0.009	0.013							
E	1.98	2.05	2.15	0.078	0.081	0.085	1.98	2.05	2.15	0.078	0.081	0.085	
E1	1.40	1.50	1.60	0.055	0.059	0.063	0.85	0.95	1.05	0.033	0.037	0.041	
E2	0.345	0.395	0.445	0.014	0.016	0.018							
E3	0.425	0.475	0.525	0.017	0.019	0.021							
е		0.65 BSC			0.026 BSC	;	0.65 BSC			0.026 BSC			
K		0.275 TYP			0.011 TYP	1	0.275 TYP			0.011 TYP			
K1		0.400 TYP			0.016 TYP		0.320 TYP			0.013 TYP			
K2		0.240 TYP		0.009 TYP		0.252 TYP			0.010 TYP				
К3		0.225 TYP		0.009 TYP									
K4		0.355 TYP			0.014 TYP								
L	0.175	0.275	0.375	0.007	0.011	0.015	0.175	0.275	0.375	0.007	0.011	0.015	
Т							0.05	0.10	0.15	0.002	0.004	0.006	
ECN: C O	07421 Pay C 06 Aug 07												

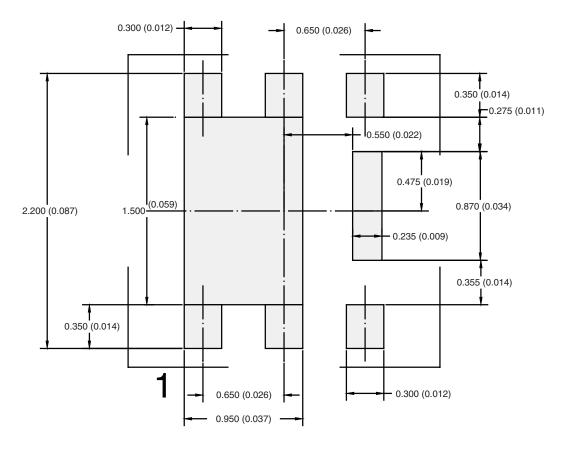
ECN: C-07431 - Rev. C, 06-Aug-07

DWG: 5934

Document Number: 73001 06-Aug-07



RECOMMENDED PAD LAYOUT FOR PowerPAK® SC70-6L Single



Dimensions in mm/(Inches)

Return to Index

ATTLICA ION NOI



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